

CLAIM AMENDMENTS

Please amend Claims 1, 3, 5, and 8, cancel Claims 2 and 10-15, and insert new Claims 16-21, as follows:

1. A semiconductor device comprising:

an insulating substrate;

a plurality of semiconductor ~~conversion~~ elements provided on the insulating substrate, for converting an energy to an electric charge;

a plurality of switching elements, the plurality of switching elements and the plurality of semiconductor conversion elements constituting a pixel area;

a plurality of drive lines connected to a gate drive device, for driving supplying a drive signal to the switching elements;

a plurality of signal lines connected to a readout device, for reading out an the electric charge ~~detected~~ converted by the semiconductor ~~conversion~~ elements provided on an insulating substrate, the semiconductor device further comprising; and

a redundant drive wiring which forms a plurality of crossings with at least one of the drive lines and the signal lines and is electrically insulated from the at least one of the drive lines and the signal lines at each crossing, outside of the pixel area, a crossings with the drive lines in an electrically insulated state and which, when the drive line has a break, is electrically connected at the crossing to the drive line having the break,

wherein one end of the redundant drive wiring is connected to the gate drive device.

2. (Cancelled)

3. (Currently Amended) The device according to Claim-~~2~~1, wherein the broken line and the redundant wiring are electrically connected by irradiating the crossing with a laser.

4. (Original) The device according to claim 1, comprising a pad on at least one of the drive lines and the signal lines.

5. (Currently Amended) The device according to Claim-~~2~~1, wherein the broken line and the redundant wiring are electrically connected by applying a voltage therebetween.

6. (Original) The device according to claim 1, wherein the redundant wiring is connected to a reference potential.

7. (Original) The device according to Claim 6, wherein the reference potential is a ground potential.

8. (Currently Amended) The device according to Claim-~~2~~1, wherein the electrical connection is effected in the crossing to fix the potential of the broken line.

9. (Original) The device according to Claim 1, wherein a semiconductor layer is formed between the drive lines and the redundant wiring or between the signal lines and the redundant wiring, at the crossings.

10. - 15 (Cancelled)

16. (New) The semiconductor device according to claim 1, wherein the semiconductor conversion element comprises a first electrode layer, an insulating layer, a first semiconductor layer, an n⁺-type semiconductor layer, and a second electrode layer, and a switching TFT comprised of a gate electrode layer, a gate insulating layer, a second semiconductor layer, and an ohmic contact layer, wherein the redundant wiring forms a plurality of crossings with at least one of the drive line and the crossings are each comprised of the insulating layer, the first semiconductor layer and the n⁺-type semiconductor layer or the gate insulating layer, the second semiconductor layer and the ohmic contact layer.

17. (New) The semiconductor device according to claim 1, wherein the semiconductor conversion element converts a light into an electric charge.

18. (New) The semiconductor device according to claim 1, wherein the semiconductor conversion element converts a radiation directly into an electric charge.

19. (New) The semiconductor device according to claim 18, wherein the semiconductor conversion element comprises amorphous selenium or GaAs.

20. (New) The semiconductor device according to claim 17, further comprising a wavelength converter for converting a radiation into the light.

21. (New) A radiation imaging system comprising:
the semiconductor device as set forth in claim 20;
signal processing means for processing a signal from the semiconductor device;

recording means for recording a signal from the signal processing means;
display means for displaying a signal from the signal processing means;
transmission processing means for transmitting a signal from the signal
processing means; and
a radiation source for generating the radiation.